Not Recommended for New Design, Use PI3EQX5801





PI2EQX4401D

2.5Gbps x1 Lane Serial PCI-Express Repeater/Equalizer with Clock Buffer & Signal Detect Feature

Features

- → One high-speed PCI-Express lane
- → Adjustable Transmiter De-Emphasis & Amplitude
- → Adjustable Receiver Equalization
- → One Spread Spectrum Reference Clock Buffer Output
- → Input Signal Level Detect and Output Squelch
- \rightarrow 100 Ω Differential CML I/O's
- → Low Power (100mW per Channel)
- → Stand-by Mode Power Down State
- → V_{DD} Operating Range: 1.8V ±0.1V
- → Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- → Halogen and Antimony Free. "Green" Device (Note 3)
- → For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative.

https://www.diodes.com/quality/product-definitions/

→ Packaging (Pb-free & Green):

— 36-pad TQFN (ZF36)

Description

Diodes' PI2EQX4401D is a low power, PCI-Express compliant signal re-driver. The device provides programmable equalization, amplification, and de-emphasis by using 4 select bits, SEL[0:3], to optimize performance over a variety of physical mediums by reducing Inter-symbol interference. PI2EQX4401D supports two 100Ω Differential CML data I/O's between the Protocol ASIC to a switch fabric, across a backplane, or extends the signals across other distant data pathways on the user's platform.

The integrated equalization circuitry provides flexibility with signal integrity of the PCI-express signal before the re-driver. Whereas the integrated de-emphasis circuitry provides flexibility with signal integrity of the PCI-express signal after the Re-Driver.

A low-level input signal detection and output squelch function is provided for both channels. Each channel operates fully independently. When a channel is enabled (EN_x=1) and operating, that channel's input signal level (on xl+/-) determines whether the output is enabled. If the input level of the channel falls below the active threshold level (Vth-) then the output driver switches off, and the pin is pulled to VDD via a high impedance resistor.

In addition to providing signal re-conditioning, Diodes' PI2EQX4401D also provides power management Stand-by mode operated by a Bus Enable pin. A differential clock buffer is provided for test and other system requirements. This clock function is not used by the data channels.

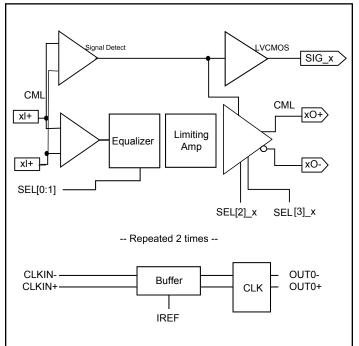
Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

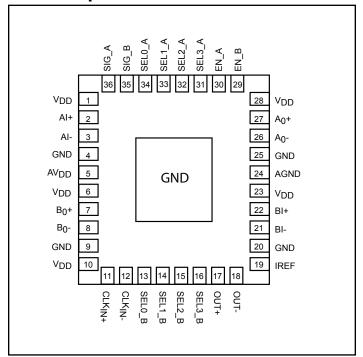




Block Diagram



Pin Description







Pin Description

Pin #	Pin Name	I/O	Description	
1, 6, 10, 23, 28	$V_{ m DD}$	PWR	1.8V Supply Voltage	
2	AI+	I	Positive CML Input Channel A with internal 50Ω pull down during normal operation (EN_A=1). When EN_A=0, this pin is high-impedance.	
3	AI-	I	Negative CML Input Channel A with internal 50Ω pull down during normal operation (EN_A=1). When EN_A=0, this pin is high-impedance.	
4, 9, 20, 25	GND	PWR	Supply Ground	
22	BI+	I	Positive CML Input Channel B with internal 50Ω pull down during normal operation (EN_B=1). When EN_B=0, this pin is high-impedance.	
21	BI-	I	Negative CML Input Channel B with internal 50Ω pull down during normal operation (EN_B=1). When EN_B=0, this pin is high-impedance.	
34, 33	SEL[0:1]_A	I	Selection pins for equalizer (see Amplifier Configuration Table)	
13, 14	SEL[0:1]_B	I	$w/50K\Omega$ internal pull up	
32	SEL[2]_A	I	Selection pins for amplifier (see Amplifier Configuration Table)	
15	SEL[2]_B	I	$w/50K\Omega$ internal pull up	
31	SEL[3]_A	I	Selection pins for De-Emphasis (See De-Emphasis Configuration Table)	
16	SEL[3]_B	I	$w/50K\Omega$ internal pull up	
27	AO+	О	Positive CML Output Channel A internal 50Ω pull up during normal operation and $2K\Omega$ pull up otherwise.	
26	AO-	О	Negative CML Output Channel A with internal 50Ω pull up during normal operat and $2K\Omega$ pull up otherwise.	
7	BO+	О	Positive CML Output Channel B with internal 50Ω pull up during normal operation and $2K\Omega$ pull up otherwise.	
8	ВО-	О	Negative CMLOutput Channel B with internal 50Ω pull up during normal operation and $2K\Omega$ pull up otherwise.	
30, 29	EN_[A,B]	I	EN_[A:B] is the enable pin. A LVCMOS high provides normal operation. A LVC-MOS low selects a low power down mode.	
12	CLKIN-	I	Differential Input Reference Clock. If clock buffer is not used, then both CLKIN+,	
11	CLKIN+	I	CLKIN- should be pulled high to VDD.	
17, 18	OUT+, OUT-	О	Differential Reference Clock Output	
5	AVDD	PWR	1.8V Analog supply voltage	
24	AGND	PWR	Analog ground	
19	IREF	О	External 475Ω resistor connection to set the differential output current. If the clock buffer is not used, then IREF should be unconnected (open).	
36, 35	SIG_A, SIG_B	О	SIG Detector output for channel A-B. Provides a LVCMOS high output when an input signal greater than the threshold is detected	





Maximum Ratings

(Above which useful life may be impaired. For user guidelines, not tested.)

Storage Temperature	-65°C to +150°C
Supply Voltage to Ground Potential	0.5V to +2.5V
DC SIG Voltage	-0.5 V to $V_{DD} + 0.5$ V
Current Output	25mA to +25mA
Power Dissipation Continous	500mW
Operating Temperature	0 to +70°C

Note

Stresses greater than those listed under MAXIMUM RAT-INGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

Output Swing Control

SEL2_[A:B]	Swing
0	1x
1	1.2x

Output De-emphasis Adjustment

SEL3_[A:B]	De-emphasis
0	0dB
1	-3.5dB

Equalizer Selection

SEL0_[A:B]	SEL1_[A:B]	Compliance Channel		
0	0	no equalization		
0	1	[0:2.5dB] @ 1.25 GHz		
1	0	[2.5:4.5dB] @ 1.25 GHz		
1	1	[4.5:6.5dB] @ 1.25 GHz		

Note:

AC/DC Electrical Characteristics ($V_{DD} = 1.8 \pm 0.1 V$)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units
D	Supply Power	EN = LVCMOS Low			0.1	117
Ps		EN = LVCMOS High			0.6	W
	Latency	From input to output		2.0		ns
CML Receive	er Input					
RL_{RX}	Return Loss	50 MHz to 1.25 GHz		12		dB
V _{RX-DIFFP-P}	Differential Input Peak-to-peak Voltage		0.175		1.200	V
V _{RX-CM-ACP}	AC Peak Common Mode Input Voltage				150	mV
V _{TH} -	Signal Detection Threshold	EN_x=High		120	175	mV
Z _{RX-DIFF-DC}	DC Differential Input Impedance		80	100	120 Ω	
Z_{RX-DC}	DC Input Impedance		40	50	60	
Equalization						
J_{RS}	Residual Jitter	Total Jitter ⁽²⁾			0.3	IIIn n
	Residual Jillel	Deterministic jitter			0.2	Ulp-p
J_{RM}	Random Jitter	See note 2		1.5		psrms

Notes

- 1. K28.7 pattern is applied differentially at point A as shown in Figure 1.
- 2. Total jitter does not include the signal source jitter. Total jitter (TJ) = (14.1 × RJ + DJ) where RJ is random RMS jitter and DJ is maximum deterministic jitter. Signal source is a K28.5 ± pattern (00 1111 1010 11 0000 0101) for the deterministic jitter test and K28.7 (0011111000) or equivalent for random jitter test. Residual jitter is that which remains after equalizing media-induced losses of the environment of Figure 1 or its equivalent. The deterministic jitter at point B must be from media-induced loss, and not from clock source modulation. Jitter is measured at 0V at point C of Figure 1.

Design target specification. Absolute values will be based on characterization.





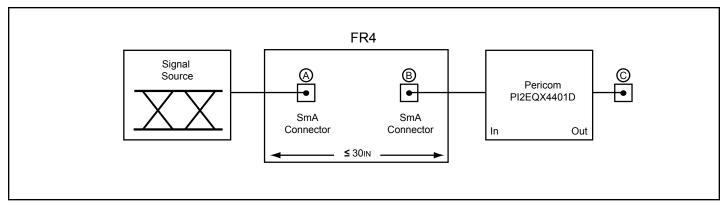


Figure 1. Test Condition Referenced in the Electrical Characteristic Table

AC/DC Electrical Characteristics (T_A = 0 to 70°C)

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Units	
CML Transmitter Output (100Ω differential)							
V _{DIFFP}	Output Voltage Swing	Differential Swing V _{TX-D+} - V _{TX-D-}	400		650	mVp-p	
V _{TX-C}	Common-Mode Voltage	V _{TX-D+} + V _{TX-D-} / 2		V _{DD} -0.3			
t _F , t _R	Transition Time	20% to 80% ⁽³⁾			150	ps	
Z _{OUT}	Output resistance	Single ended	40	50	60	Ω	
Z _{TX-DIFF-DC}	DC Differential TX Impedance		80	100	120	Ω	
C_{TX}	AC Coupling Capacitor		75		200	nF	
V _{TX-DIFFP-P}	Differential Peak-to-peak Ouput Voltage	$V_{TX-DIFFP-P} = 2 * V_{TX-D+} - V_{TX-D-} $	0.8		1.3	V	
LVCMOS Co	ontrol Pins						
V _{IH}	Input High Voltage		$0.65 \times V_{DD}$		V_{DD}	V	
V _{IL}	Input Low Voltage				$0.35 \times V_{DD}$]	
I_{IH}	Input High Current 250		250				
I_{IL}	Input Low Current				500	μΑ	

Notes

- 3. Using K28.7 (0011111000) patern)
- 4. AC specifications are guaranteed by design and characterization





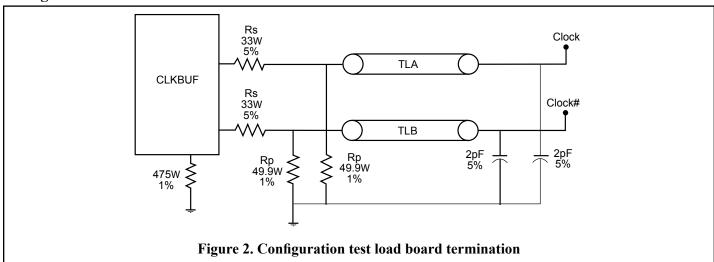
AC Switching Characteristics for Clock Buffer (V_{DD} = 1.8 ±0.1V, AV_{DD} = 1.8 ±0.1V)

Symbol	Parameters		Max.	Units	Notes
T _{rise} / T _{fall}	Rise and Fall Time (measured between 0.175V to 0.525V)		525		1
ΔT_{rise} / ΔT_{fall}	Rise and Fall Time Variation		75	ps	1
V_{HIGH}	Voltage High including overshoot		900		1
$V_{ m LOW}$	Voltage Low including undershoot			mV	1
V _{CROSS}	Absolute crossing point voltages		550	IIIV	1
ΔV_{CROSS}	Total Variation of Vcross over all edges		250		1
T_{DC}	Duty Cycle (input duty cycle = 50%)		55	%	2

Notes:

- 1. Measurement taken from Single Ended waveform.
- 2. Measurement taken from Differential waveform.
- 3. Test configuration is $R_S = 33.2\Omega$, $Rp = 49.9\Omega$, and 2pF.

Configuration Test Load Board Termination



Note: TLA and TLB are 3" transmission lines.

Part Marking

ZF Package



W: Die Rev YY: Year

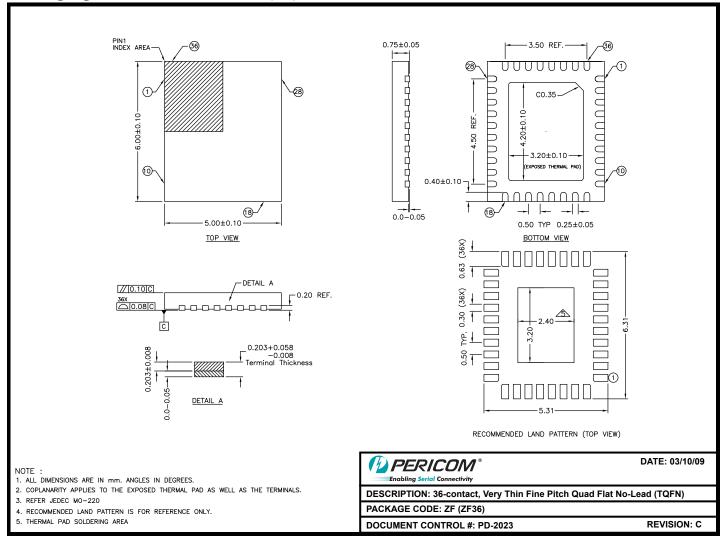
WW: Workweek

1st X: Assembly Code 2nd X: Fab Code





Packaging Mechanical: 36-TQFN (ZF)



09-0143

For latest package info.

please check: http://www.diodes.com/design/support/packaging/pericom-packaging/packaging-mechanicals-and-thermal-characteristics/

Ordering Information

Ordering Number Package Code		Package Description			
PI2EQX4401DZFEX	ZF	36-contact, Very Thin Fine Pitch Quad Flat No-Lead (TQFN)			

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. E = Pb-free and Green
- 5. X suffix = Tape/Reel





IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel.

Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
 - 1. are intended to implant into the body, or
- 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2016, Diodes Incorporated www.diodes.com